

Silicon Triple Diffused Planar Transistor

TOP-3 Package

T-33-13

2SD917(NPN)**2SD917 (NPN)****Absolute Maximum Ratings (Ta=25°C)**

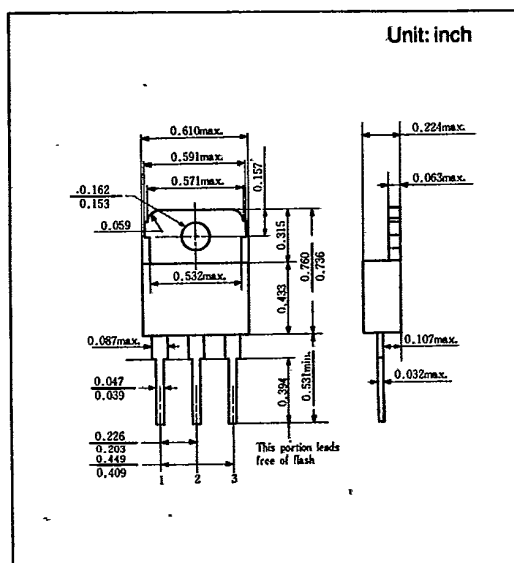
Item	Symbol	Rating	Unit
Collector-Base Voltage	V _{CB0}	330	V
Collector-Emitter Voltage	V _{CE0}	200	V
Emitter-Base Voltage	V _{EB0}	6	V
Peak Collector Current	I _{CM}	10	A
Collector Current	I _C	7	A
Collector Power Dissipation	P _C *	70	W
Junction Temperature	T _J	150	°C
Storage Temperature	T _{stg}	-55~+150	°C

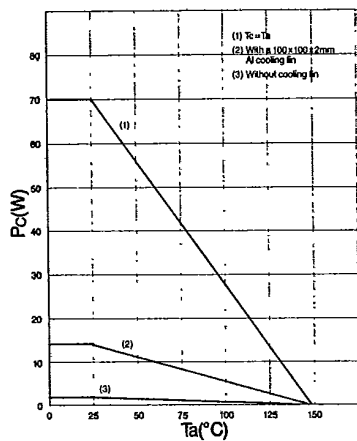
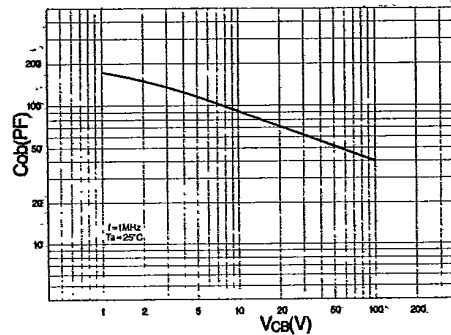
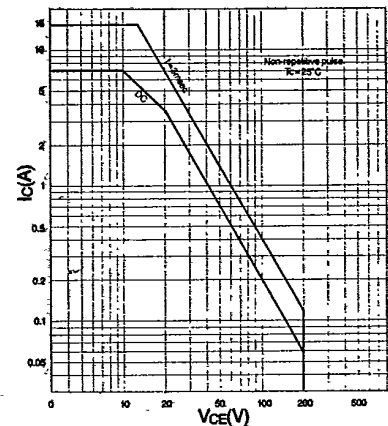
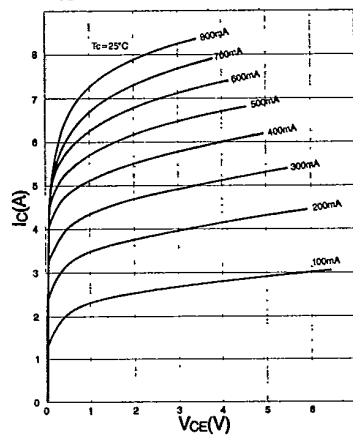
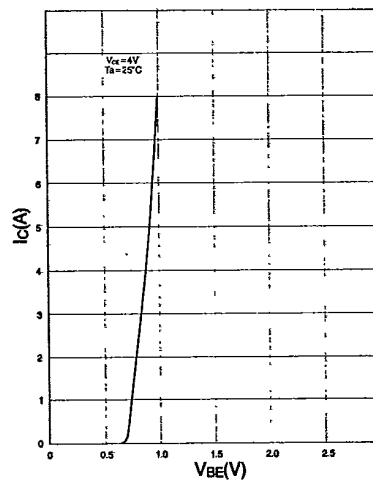
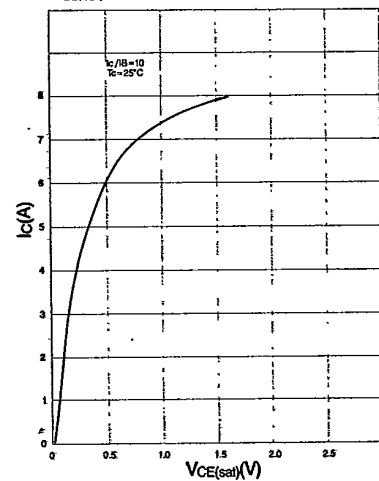
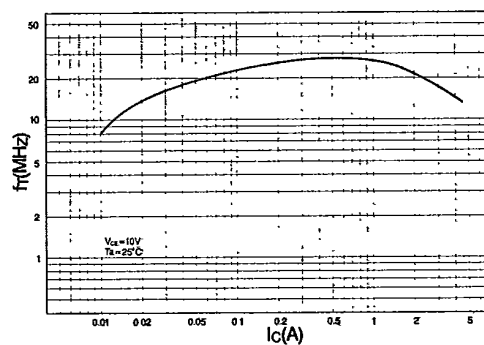
*T_C=25°C**High Power TV Deflection****Feature:**

- High collector power dissipation: 70W(T_C=25°C)

Electrical Characteristics (Ta=25°C)

Item	Symbol	Condition	min.	max.	Unit
Emitter Cutoff Current	I _{EB0}	V _{EB} =6V, I _C =0		1	mA
DC Current Gain	h _{FE}	V _{CE} =4V, I _C =5A	15	45	—
Base Emitter Voltage	V _{BE}	I _C =5A, I _B =0.5A		1.2	V
Collector-Emitter Saturation Voltage	V _{CE(sat)}	I _C =5A, I _B =0.5A		1	V
Gain Bandwidth Product	f _T	I _C =5A, I _B =0.5A		0.75	μS
Emitter-Collector Current, Base Shorted	I _{CES}	V _{CE} =330V, V _{BE} =0		0.1	mA
Emitter-Collector Current, Base Shorted	I _{CES}	V _{CE} =300V, V _{BE} =0, Ta=100°C		1	mA
Thermal Resistance Junction to Ambient	R _{TH}			1.8	°C/W

TOP-3 Package Dimensions

2SD917(NPN)**Typical Characteristics****P_C vs. T_a characteristics****C_{ob} vs. V_{CB} characteristics****Area of Safe Operation (ASO) ($T_C = 25^{\circ}\text{C}$)****V_{CE} vs. I_C characteristics****V_{BE} vs. I_C characteristics****V_{CE(sat)} vs. I_C characteristics****f_T vs. I_C characteristics****h_{FE} vs I_C characteristics**